

FEATURES

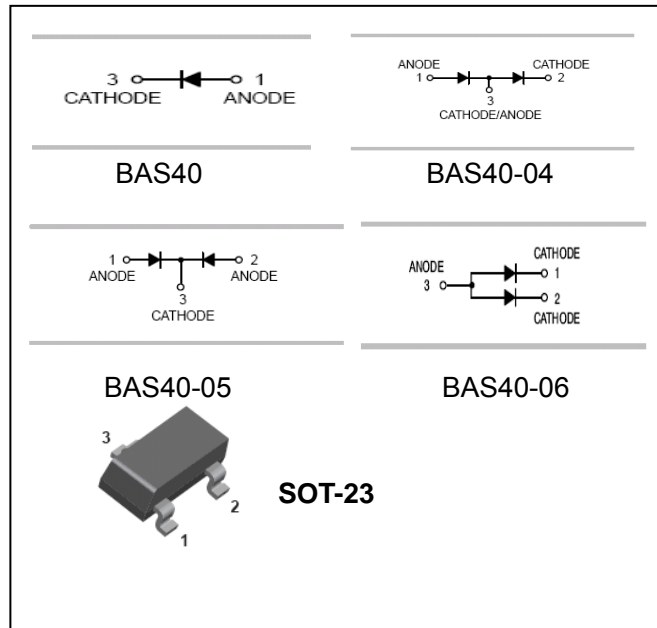
- Low turn-on voltage.
- Fast switching.
- PN Junction guard ring for transient and ESD protection.



Lead-free

APPLICATIONS

- High speed switching applications.
- Circuit protecting.
- Voltage clamping.



ORDERING INFORMATION

Type No.	Marking	Package Code
BAS40	43	SOT-23
BAS40-04	44	SOT-23
BAS40-05	45	SOT-23
BAS40-06	46	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Limits	Unit
Peak Repetitive Reverse Voltage	V_{RRM}		
Working Peak Reverse Voltage	V_{RWM}	40	V
DC Reverse Voltage	V_R		
Forward Continuous Current	I_{FM}	200	mA
Power Dissipation	P_d	350	mW
Forward Surge	I_{FSM}	600	mA
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	357	°C/W
Operating Junction Temperature Range	T_j	-55 to +125	°C
Storage Temperature Range	T_{STG}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

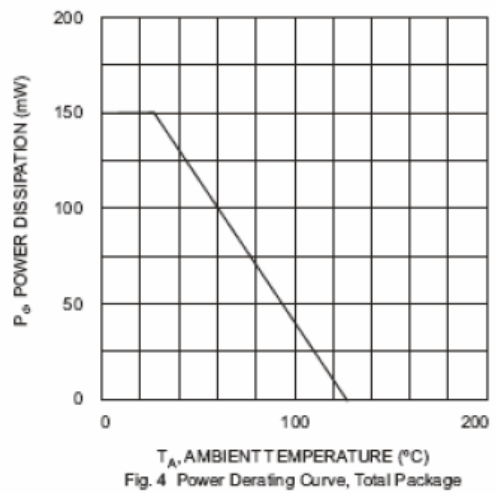
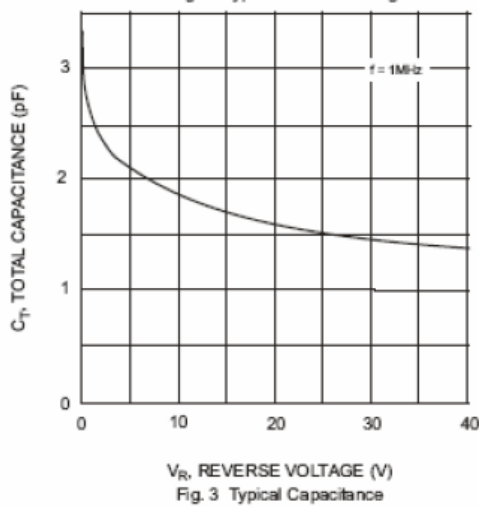
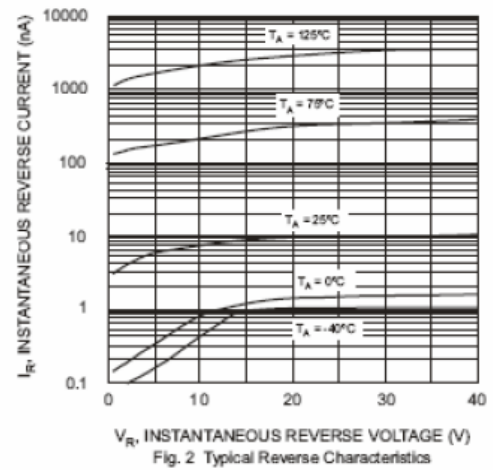
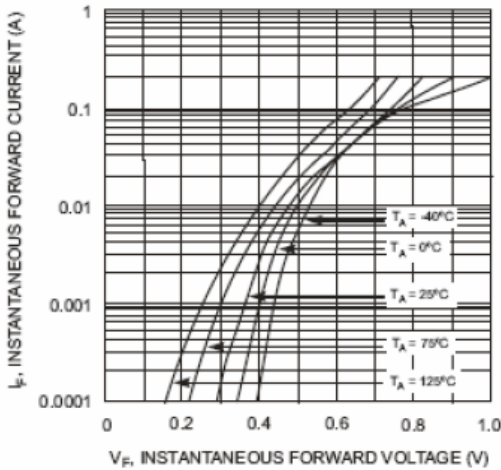
Diode Semiconductor Korea

Surface mount schottky barrier diode

BAS40/-04/-05/-06

Characteristic	Symbol	Min	Typ	MAX	UNIT	Test Condition
Reverse Breakdown Voltage	$V_{(BR)R}$	40	-	-	V	$I_{RS} = 10\mu A$
Forward Voltage	V_F	-	-	380 1000	mV	$t_P < 300\mu s, I_F = 1.0mA$ $t_P < 300\mu s, I_F = 40mA$
Reverse Leakage Current	I_R	-	20	200	nA	$t_P < 300\mu s, V_R = 30V$
Junction Capacitance	C_j	-	4.0	5.0	pF	$V_R = 0V, f = 1.0MHz$
Reverse Recovery Time	t_{rr}	-	-	5.0	ns	$I_F = I_R = 10mA$ to $I_R = 1.0mA, R_L = 100\Omega$

TYPICAL CHARACTERISTICS @ $T_a = 25^\circ C$ unless otherwise specified



Diode Semiconductor Korea

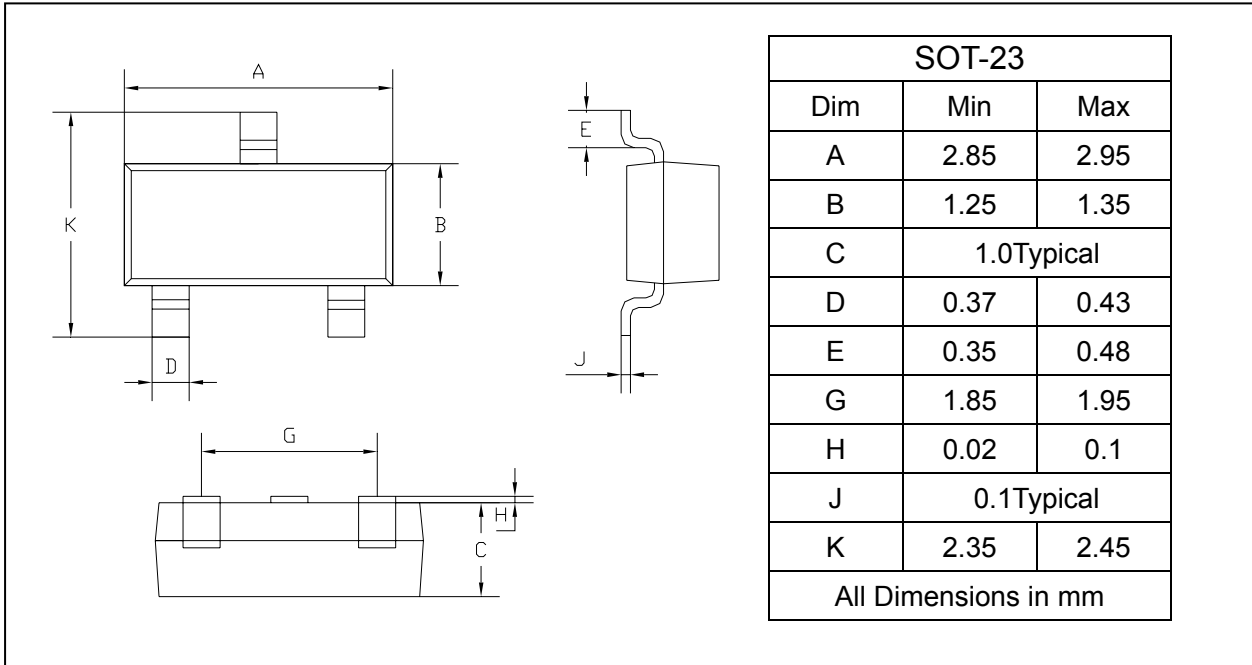
Surface mount schottky barrier diode

BAS40/-04/-05/-06

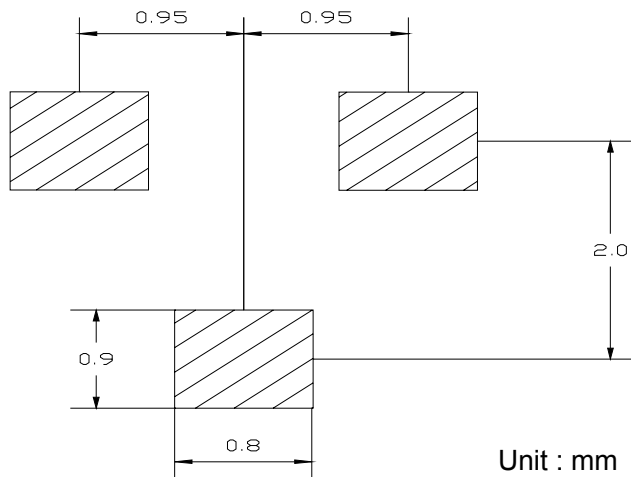
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BAS40/-04/-05/-06	SOT-23	3000/Tape&Reel